

## 1. Global joint venture starts operations as WeEn Semiconductors

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WeEn Semiconductors



**Product data sheet** 

# 1. General description

Hyperfast power diode in a SOD59 package.

## 2. Features and benefits

- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT

# 3. Applications

- Half-bridge/full-bridge switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage			-	-	600	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5; T <sub>mb</sub> ≤ 133 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		-	-	5	А
Static characte	eristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	2.5	3.3	V
		I <sub>F</sub> = 5 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.4	2.1	V
Dynamic characteristics							
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	11	-	ns





Hyperfast power diode

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode	}	001aaa020
mb	mb	mounting base; connected to cathode	TO-220AC (SOD59)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BYC5-600P	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59			

# 7. Marking

Table 4. Marking codes

Type number	Marking code
BYC5-600P	BYC5-600P

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# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	600	V
$V_{RWM}$	crest working reverse voltage		-	600	V
$V_R$	reverse voltage	DC	-	600	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5; T <sub>mb</sub> ≤ 133 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	5	A
I <sub>FRM</sub>	repetitive peak forward current	$δ$ = 0.5; $t_p$ = 25 μs; $T_{mb}$ ≤ 133 °C; square-wave pulse	-	10	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	60	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	65	Α
T <sub>stg</sub>	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

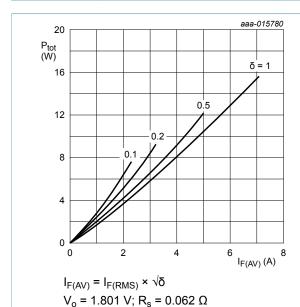


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

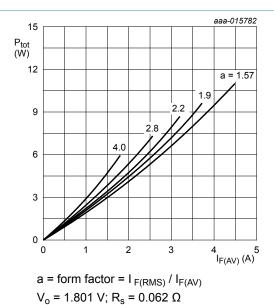


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

### Hyperfast power diode

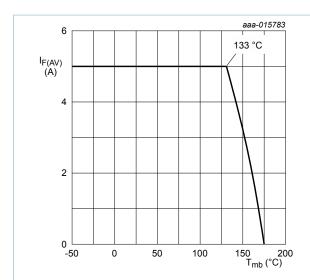


Fig. 3. Forward current as a function of mounting base temperature; maximum values

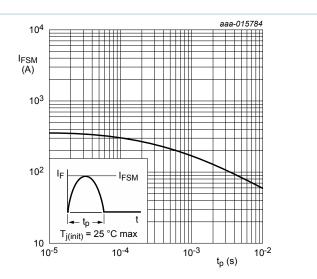


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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Hyperfast power diode

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	3.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W

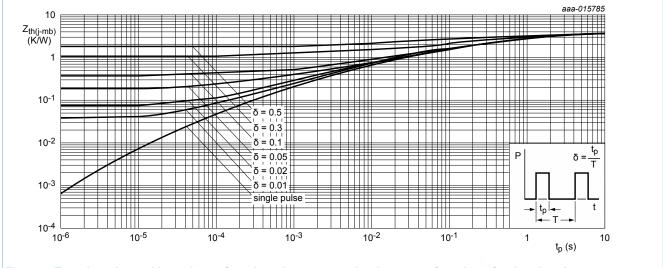


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

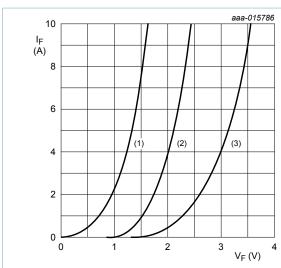
Hyperfast power diode

# 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>F</sub> f	forward voltage	I <sub>F</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	2.5	3.3	V
		I <sub>F</sub> = 5 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	1.4	2.1	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 150 °C	-	-	0.6	mA
Dynamic ch	naracteristics		'			
Q <sub>r</sub> recovered charge	recovered charge	$I_F = 5 \text{ A}$ ; $V_R = 200 \text{ V}$ ; $dI_F/dt = 200 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7	-	19	-	nC
	$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	45	-	nC	
t <sub>rr</sub> reverse rec	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	11	-	ns
		$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	23	-	ns
		$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	28	-	ns
		$I_F = 5 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	13	25	ns
	peak reverse recovery current	$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	1.7	-	Α
		I <sub>F</sub> = 5 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>	-	3.2	-	Α

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 $V_o$  = 1.801 V;  $R_s$  = 0.062  $\Omega$ 

(1) T<sub>j</sub> = 150 °C; typical values

(2)  $T_j$  = 150 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage

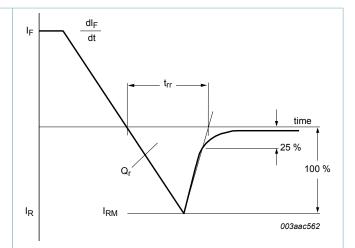
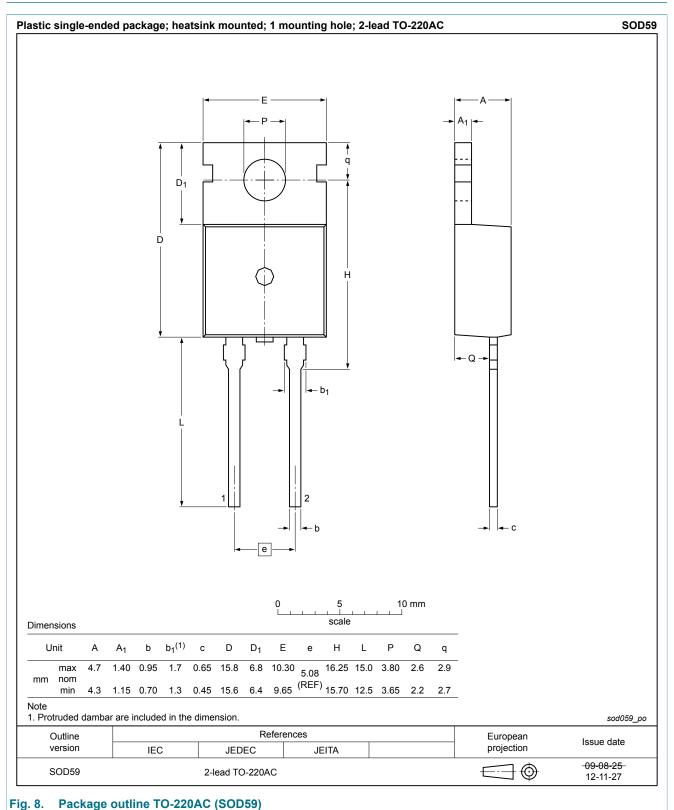


Fig. 7. Reverse recovery definitions; ramp recovery

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# 11. Package outline



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#### Hyperfast power diode

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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